优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
50V	40mΩ @ V_{GS} = 10V	5.2A
	60mΩ @ V_{GS} = 4.5V	4.3A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed

Description and Applications

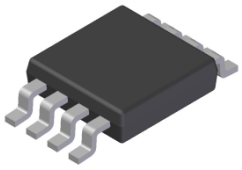
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- Backlighting
- Power Management Functions
- DC-DC Converters

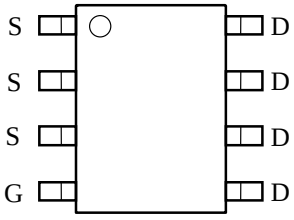
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram Below
- Terminals: Finish — Matte Tin Annealed Over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.074 grams (Approximate)

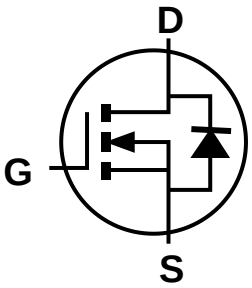
SO-8



Top View



Top View
Internal Schematic



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	50	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	5.2 4.2	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I_{DM}	25	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	1.8	A
Avalanche Current (Note 7) L = 0.1mH			I_{AS}	13	A
Avalanche Energy (Note 7) L = 0.1mH			E_{AS}	8	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5) (T_A = +25°C)	Steady State	P_D	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	99	°C/W
Total Power Dissipation (Note 6) (T_A = +25°C)	Steady State	P_D	1.6	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	77	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	13	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	50	-	-	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1	μA	V_{DS} = 50V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	-	3.0	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	29	40	mΩ	V_{GS} = 10V, I_D = 4.5A
		-	37	60		V_{GS} = 4.5V, I_D = 3.5A
Diode Forward Voltage	V_{SD}	-	0.7	1.2	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	-	836	-	pF	V_{DS} = 30V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	42	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	28	-	pF	
Gate Resistance	R_g	-	2.2	-	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	-	6.5	-	nC	V_{DS} = 30V, I_D = 5A
Total Gate Charge (V_{GS} = 10V)	Q_g	-	14.5	-	nC	
Gate-Source Charge	Q_{gs}	-	2.0	-	nC	
Gate-Drain Charge	Q_{gd}	-	2.3	-	nC	
Turn-On Delay Time	$t_{D(ON)}$	-	3.1	-	ns	V_{DD} = 30V, V_{GS} = 10V, R_L = 6Ω, R_g = 6Ω, I_D = 5A
Turn-On Rise Time	t_R	-	5.0	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	13.4	-	ns	
Turn-Off Fall Time	t_F	-	3.7	-	ns	
Reverse Recovery Time	t_{RR}	-	9.4	-	ns	I_F= 5A, di/dt=100A/μs
Reverse Recovery Charge	Q_{RR}	-	3.7	-	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

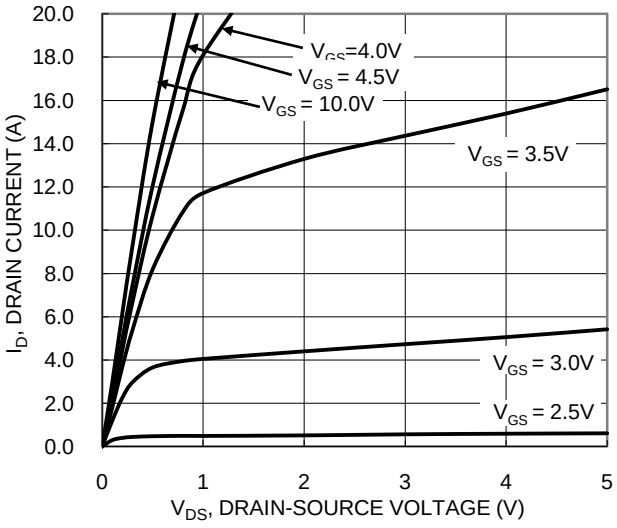


Figure 1. Typical Output Characteristic

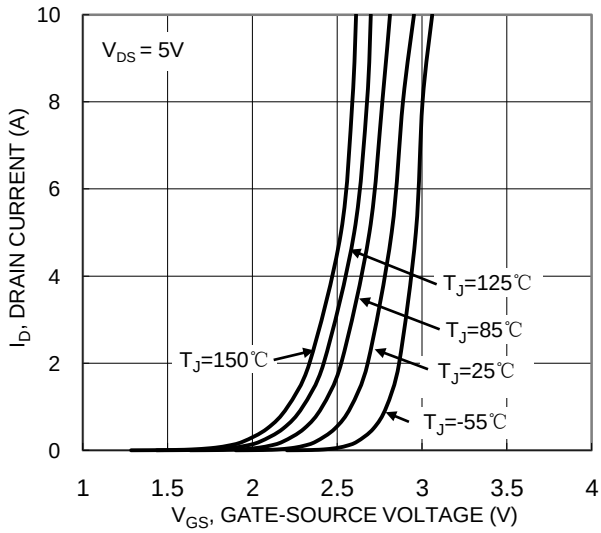


Figure 2. Typical Transfer Characteristic

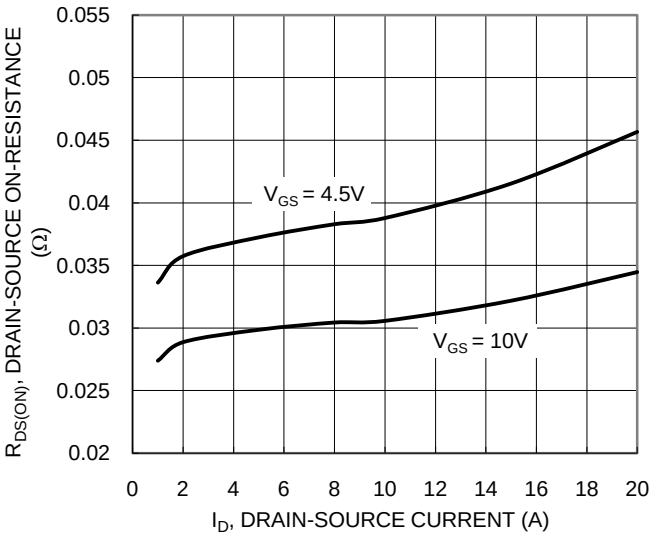


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

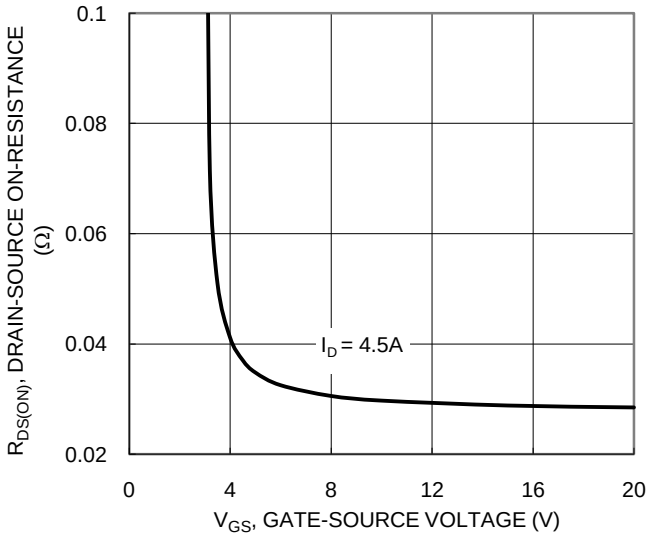


Figure 4. Typical Transfer Characteristic

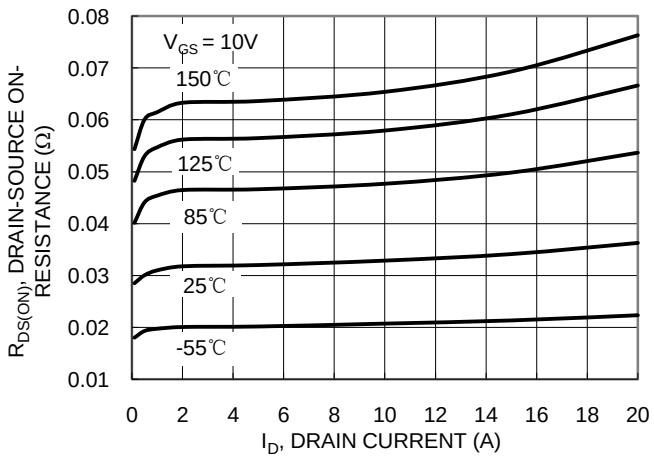


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

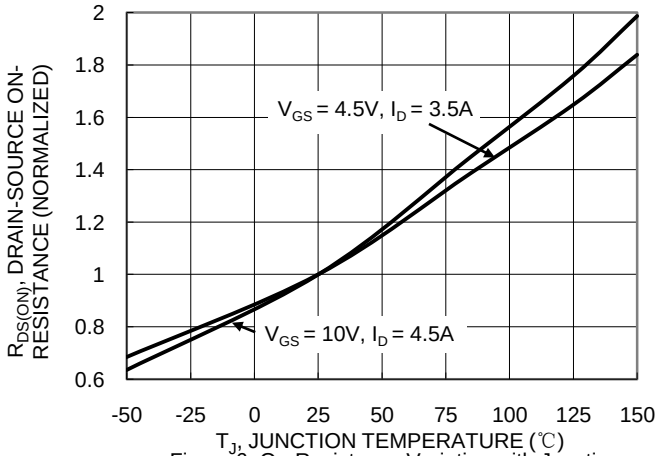


Figure 6. On-Resistance Variation with Junction Temperature

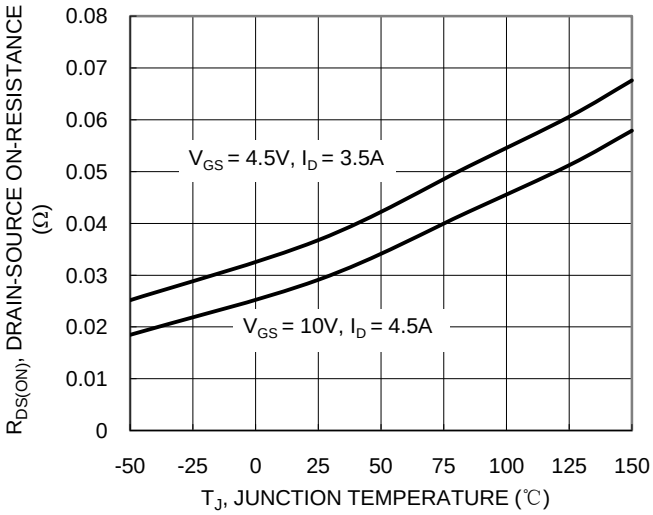


Figure 7. On-Resistance Variation with Junction Temperature

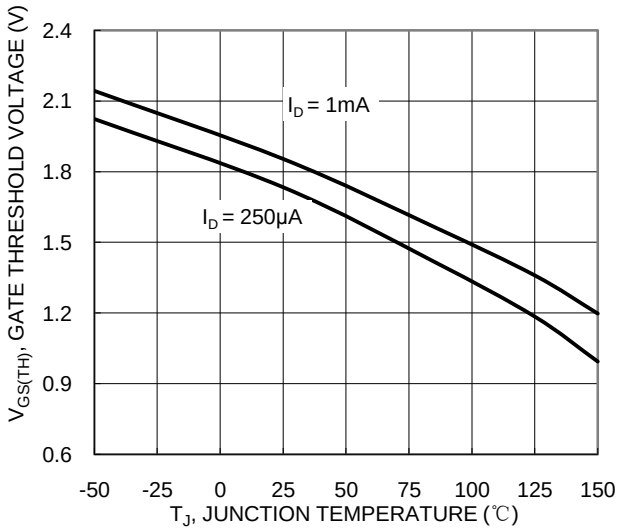


Figure 8. Gate Threshold Variation vs. Junction Temperature

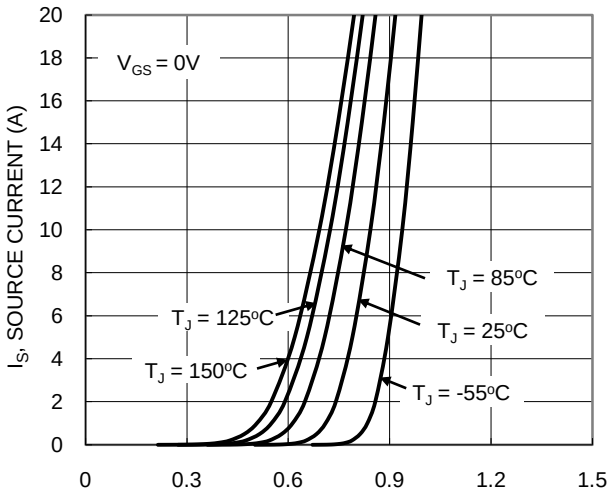


Figure 9. Diode Forward Voltage vs. Current

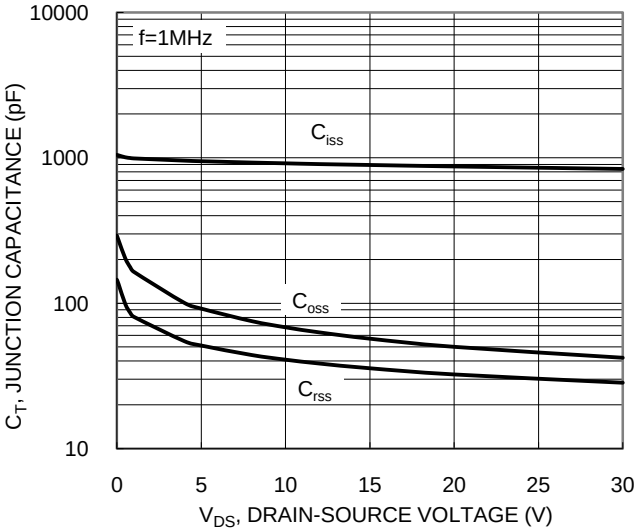


Figure 10. Typical Junction Capacitance

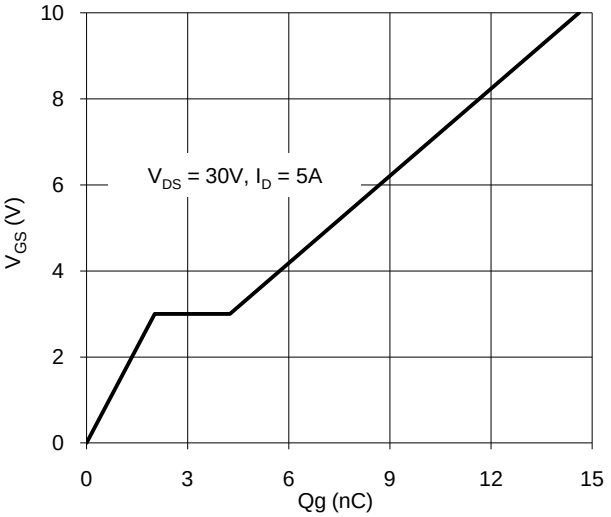


Figure 11. Gate Charge

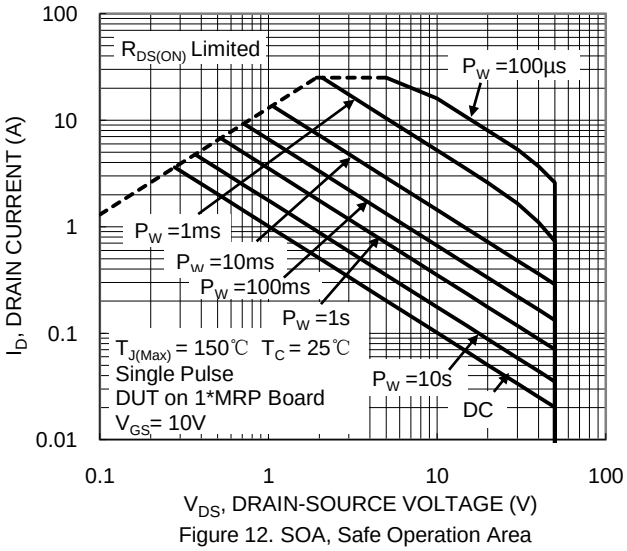


Figure 12. SOA, Safe Operation Area

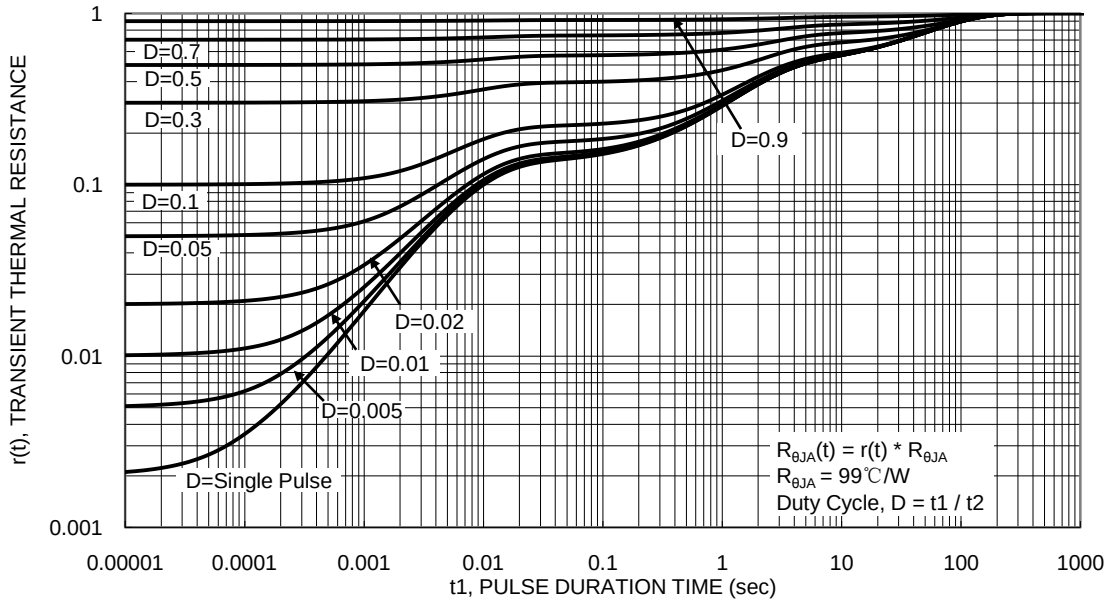
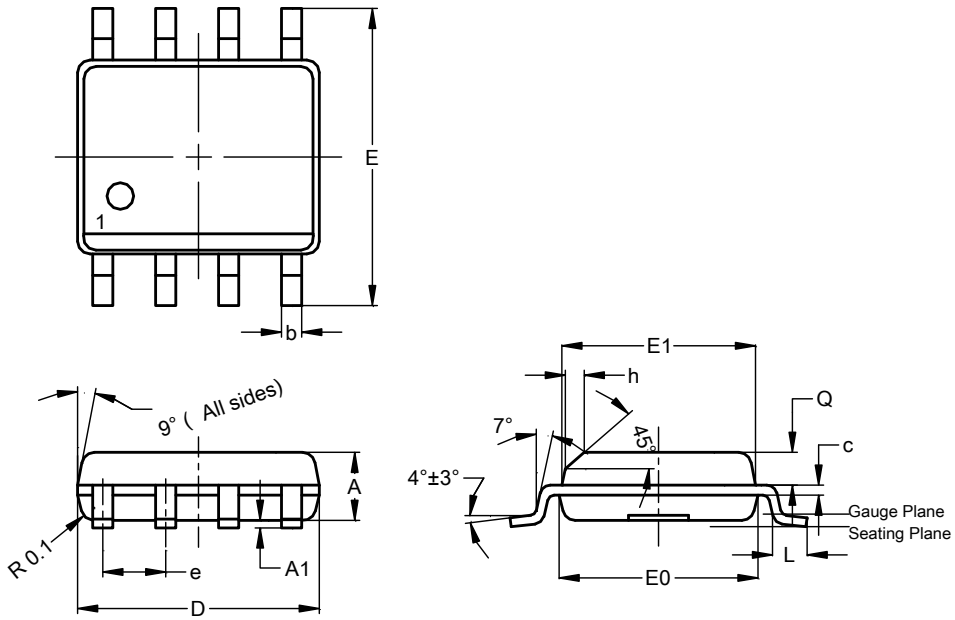


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

SO-8



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Dim	**Min**	**Max**	**Typ**
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

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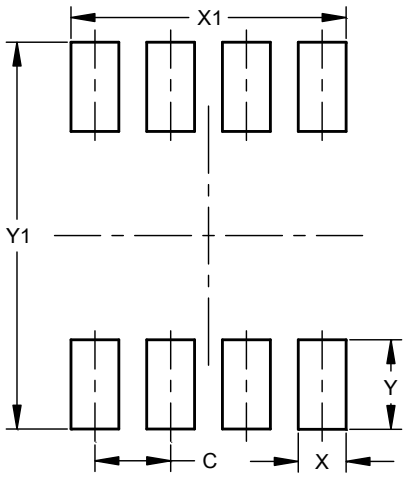

Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50